Vincotech

10-PC124PA030MS-L629F76Y
datasheet

fastPACK 0 SiC **1200 V / 30 mΩ**

Topology features

- Dual halfbridge
- Integrated DC capacitor
- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al_2O_3
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

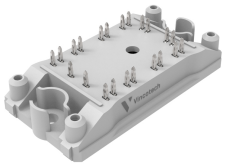
Target applications

- Charging Stations
- Energy Storage Systems
- Power Supply
- Solar Inverters
- UPS
- Welding & Cutting

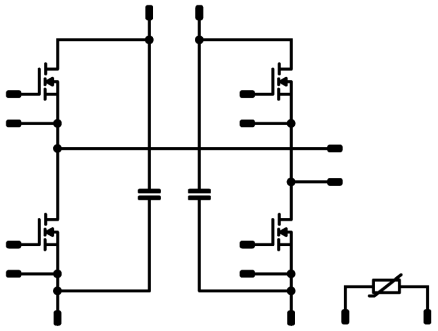
Types

- 10-PC124PA030MS-L629F76Y

flow 0 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	T_j = T_{jmax} T_s = 80 °C	40	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	160	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	76	W
Gate-source voltage	V_{GSS}	static	-5 / 18	V
		dynamic	-10 / 22	V
Maximum Junction Temperature	T_{jmax}		175	°C
Capacitor (DC)				
Maximum DC voltage	V_{MAX}		1000	V
Operation Temperature	T_{op}		... 125	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			9,19	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		18		40	25 125 150		33,2 41,4 45,7	45(1)	mΩ
Gate-source threshold voltage	$V_{GS(th)}$				0,004	25	1,7	2,25	2,75	V
Gate to Source Leakage Current	I_{GSS}		22	0		25			100	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25			10	µA
Internal gate resistance	r_g							2		Ω
Gate charge	Q_g		-5/18	800	40	25		108		nC
Short-circuit input capacitance	C_{iss}	f = 500 kHz	0	800	0	25		2600		pF
Short-circuit output capacitance	C_{oss}							135		
Reverse transfer capacitance	C_{rss}							6		
Diode forward voltage	V_{SD}		0		40	25		4,1		V
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 5,2 W/mK (PTM)						1,25		K/W

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	-4/18	600	40	25 125 150		20,36 18,04 16,98		ns
Rise time	t_r					25 125 150		14,58 12,51 12,43		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		55,52 65,02 67,29		ns
Fall time	t_f					25 125 150		15,92 15,87 16		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,234 µC Q_{rFWD}=0,67 µC Q_{rFWD}=0,807 µC				25 125 150		0,719 0,832 0,885		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,097 0,11 0,114		mWs
Peak recovery current	I_{RRM}	di/dt=2630 A/µs di/dt=3888 A/µs di/dt=3810 A/µs				25 125 150		27,29 38,48 42,85		A
Reverse recovery time	t_{rr}					25 125 150		15,72 28,55 29,11		ns
Recovered charge	Q_r					25 125 150		0,234 0,67 0,807		µC
Reverse recovered energy	E_{rec}					25 125 150		0,013 0,121 0,156		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		4187,26 1992,84 2874,64		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Capacitor (DC)										
Static										
Capacitance	C	DC bias voltage = 0 V				25		2,2		nF
Tolerance							-5		5	%
Dissipation factor		f = 1 kHz				25		1,5		%
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

(1) Value at chip level

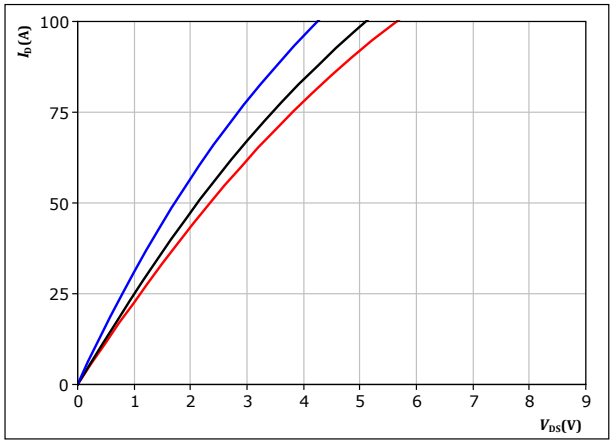
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$



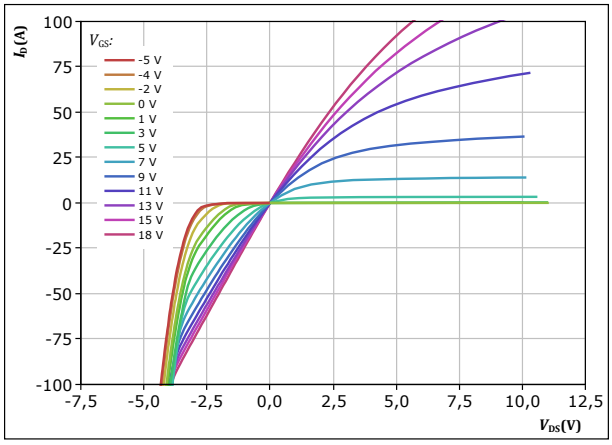
t_p = 250 µs
V_{GS} = 18 V

T_j: 25 °C, 125 °C, 150 °C

figure 2. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$

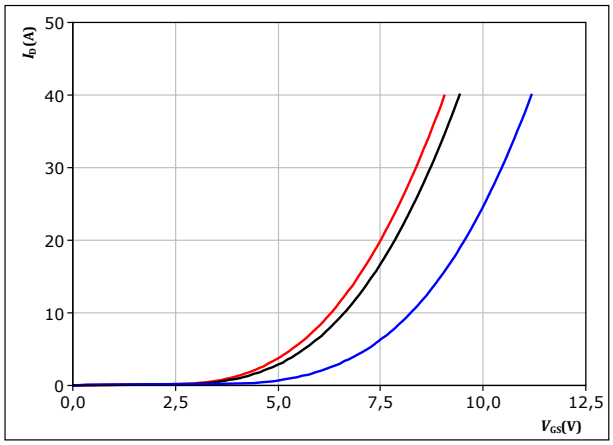


t_p = 250 µs
T_j = 150 °C
V_{GS} from -5 V to 18 V in steps of 1 V

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$



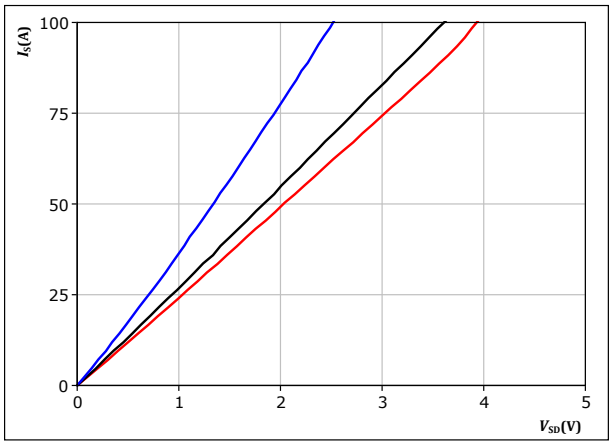
t_p = 250 µs
V_{DS} = 10 V

T_j: 25 °C, 125 °C, 150 °C

figure 4. **MOSFET**

Typical reverse drain current characteristics

$I_{SD} = f(V_{SD})$



t_p = 250 µs
V_{GS} = 18 V

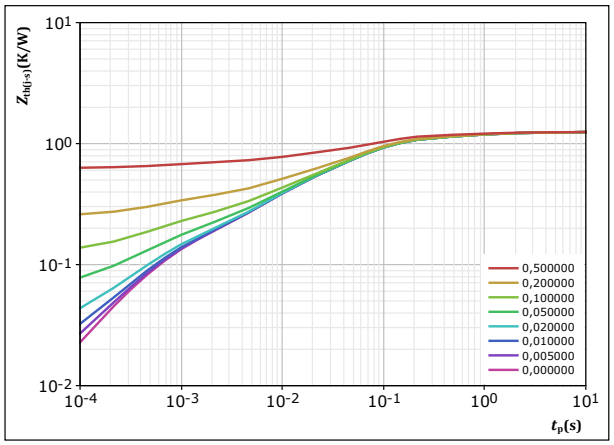
T_j: 25 °C, 125 °C, 150 °C

Inverter Switch Characteristics

figure 5. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	1,247	K/W

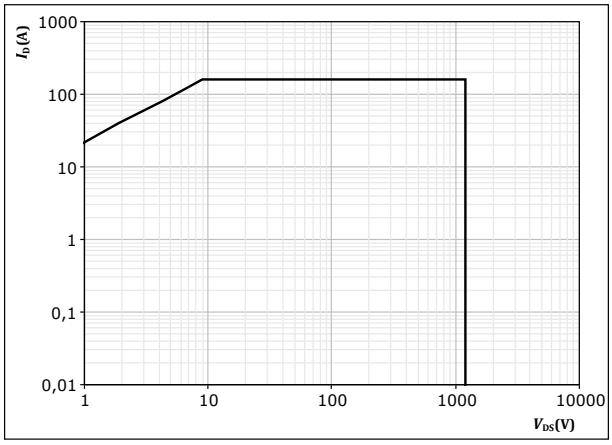
MOSFET thermal model values

R (K/W)	τ (s)
3,94E-02	4,92E+00
1,67E-01	5,65E-01
6,96E-01	6,37E-02
2,35E-01	7,82E-03
1,14E-01	5,59E-04

figure 6. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



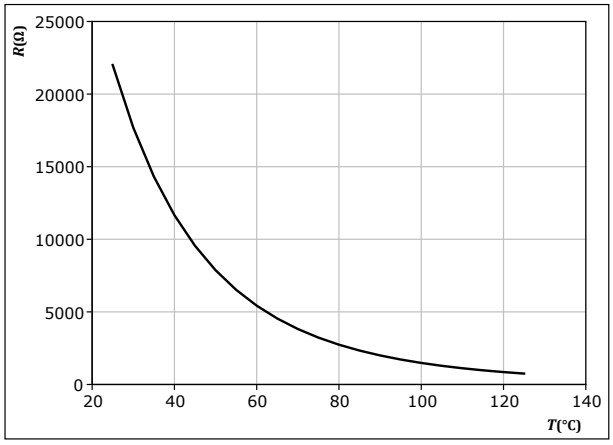
D =	single pulse	
T_s =	80	°C
V_{GS} =	18	V
T_j =	T_{jmax}	

Thermistor Characteristics

figure 7. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

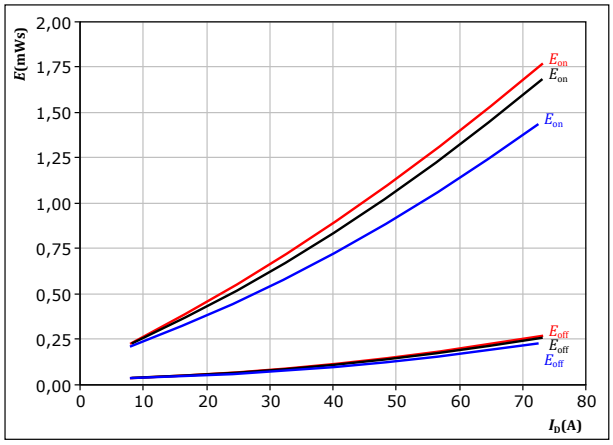


Inverter Switching Characteristics

figure 8. **MOSFET**

Typical switching energy losses as a function of drain current

E = f(I_D)



With an inductive load at

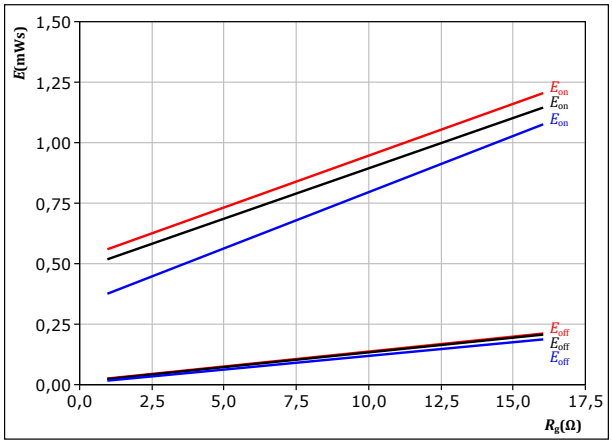
V_{DS} =	600	V	
V_{GS} =	-4/18	V	
R_{gon} =	8	Ω	
R_{goff} =	8	Ω	

T_j: 25 °C, 125 °C, 150 °C

figure 9. **MOSFET**

Typical switching energy losses as a function of MOSFET turn on gate resistor

E = f(R_g)



With an inductive load at

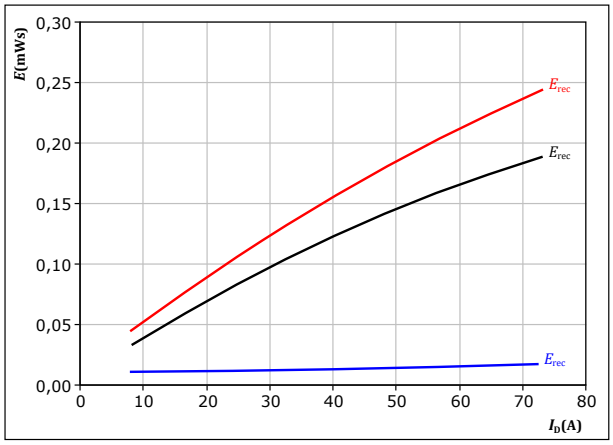
V_{DS} =	600	V	
V_{GS} =	-4/18	V	
I_D =	40	A	

T_j: 25 °C, 125 °C, 150 °C

figure 10. **MOSFET**

Typical reverse recovered energy loss as a function of drain current

E_{rec} = f(I_D)



With an inductive load at

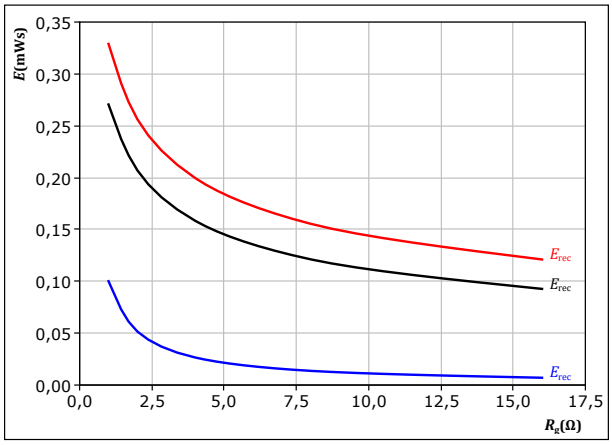
V_{DS} =	600	V	
V_{GS} =	-4/18	V	
R_{gon} =	8	Ω	

T_j: 25 °C, 125 °C, 150 °C

figure 11. **MOSFET**

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

V_{DS} =	600	V	
V_{GS} =	-4/18	V	
I_D =	40	A	

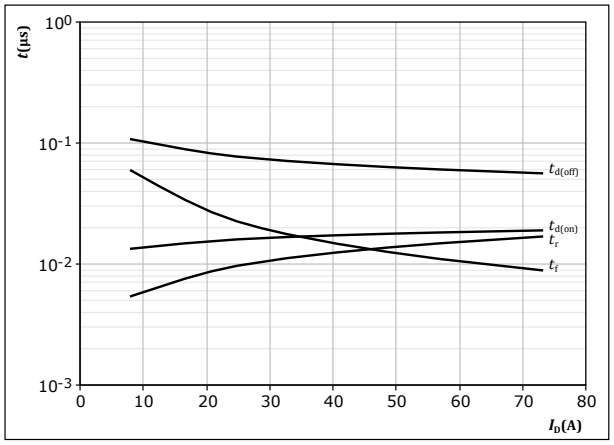
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 12. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



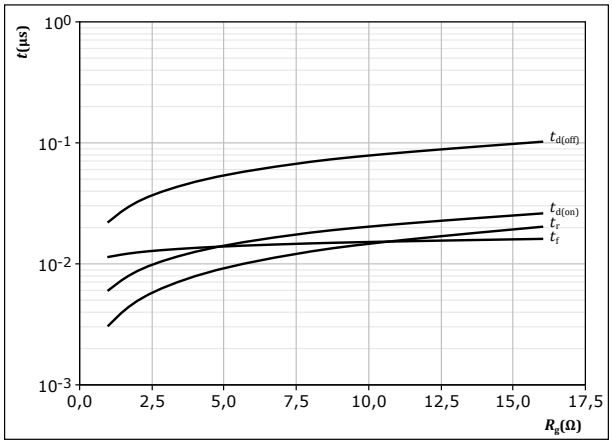
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/18	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 13. **MOSFET**

Typical switching times as a function of MOSFET turn on gate resistor

$t = f(R_g)$



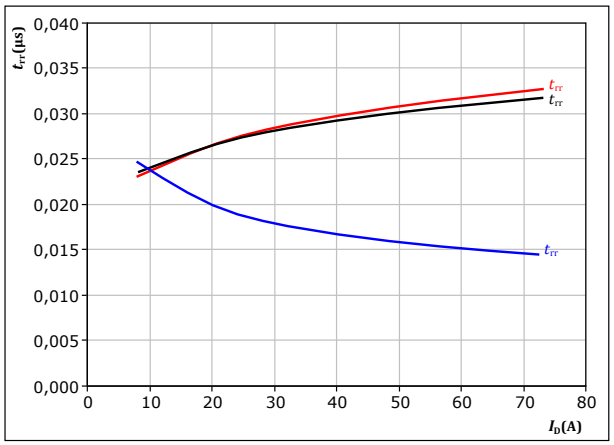
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/18	V
I_D =	40	A

figure 14. **MOSFET**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



At

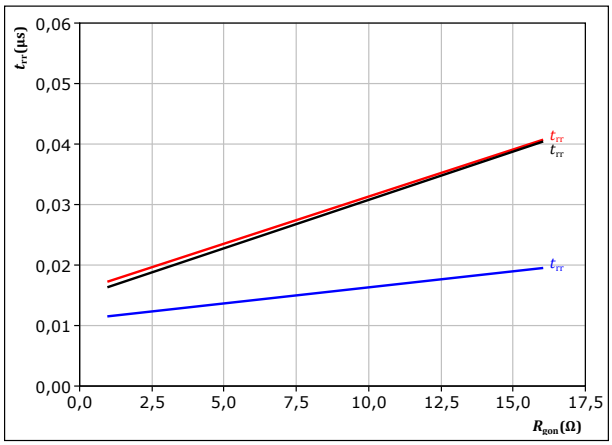
V_{DS} =	600	V
V_{GS} =	-4/18	V
R_{gon} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 15. **MOSFET**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

$t_{rr} = f(R_{gon})$



At

V_{DS} =	600	V
V_{GS} =	-4/18	V
I_D =	40	A

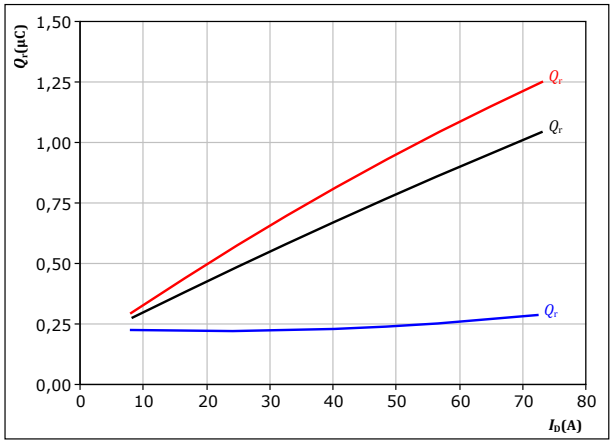
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 16. **MOSFET**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

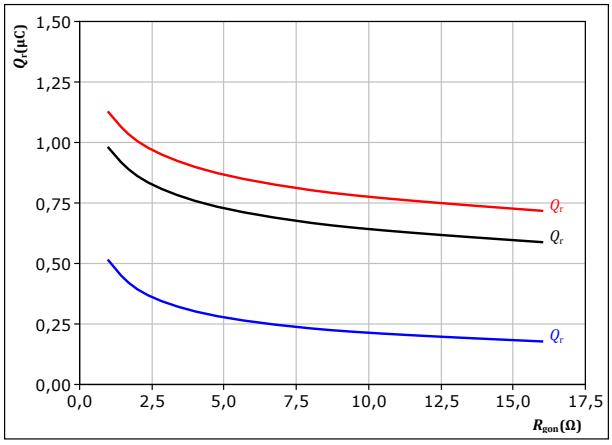


At				T_j:	
	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/18	V		125 °C
	R_{gon} =	8	Ω		150 °C

figure 17. **MOSFET**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$

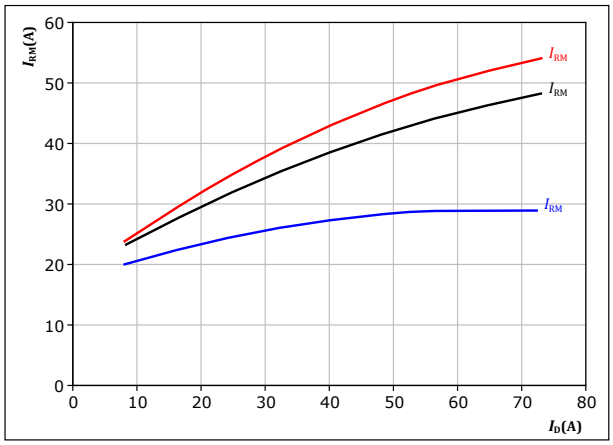


At				T_j:	
	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/18	V		125 °C
	I_D =	40	A		150 °C

figure 18. **MOSFET**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

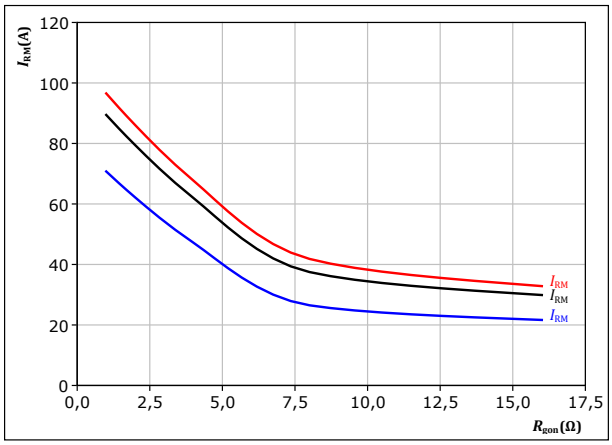


At				T_j:	
	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/18	V		125 °C
	R_{gon} =	8	Ω		150 °C

figure 19. **MOSFET**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



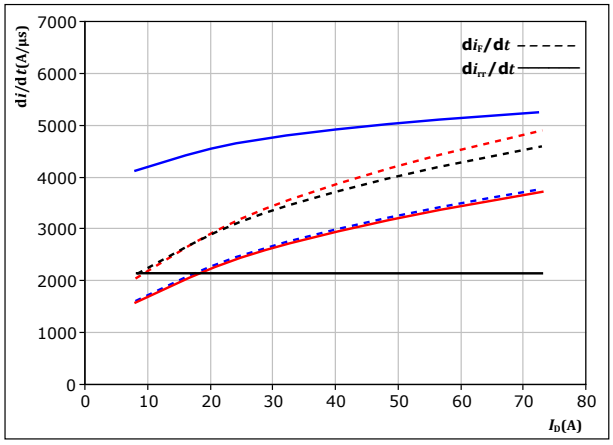
At				T_j:	
	V_{DS} =	600	V		25 °C
	V_{GS} =	-4/18	V		125 °C
	I_D =	40	A		150 °C

Inverter Switching Characteristics

figure 20. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

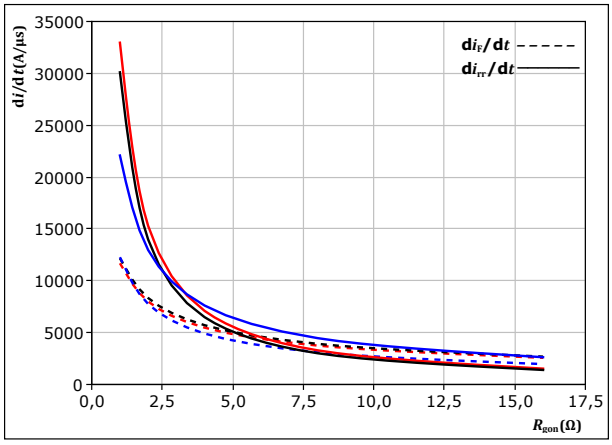


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/18	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 21. **MOSFET**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

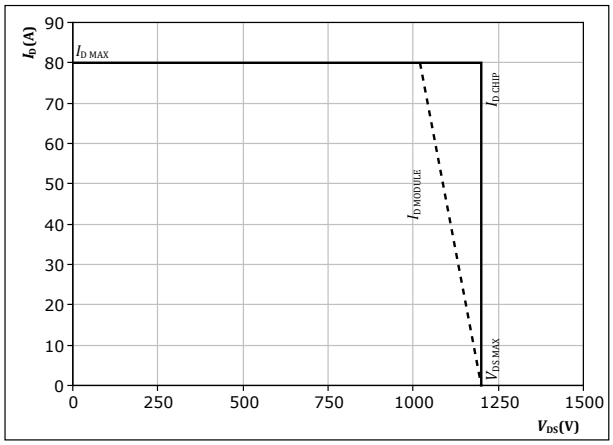


At				
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/18	V		125 °C
I_D =	40	A		150 °C

figure 22. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At			
T_j =	150	°C	
R_{gon} =	8	Ω	
R_{goff} =	8	Ω	

Inverter Switching Definitions

figure 23. MOSFET

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

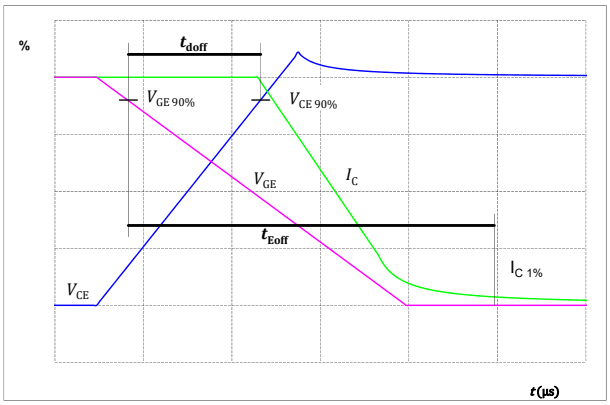


figure 24. MOSFET

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

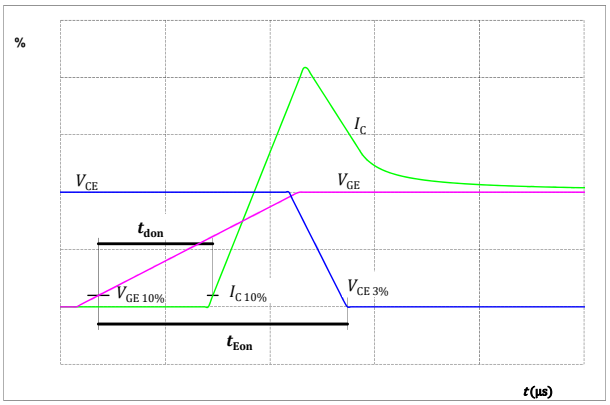


figure 25. MOSFET

Turn-off Switching Waveforms & definition of t_f

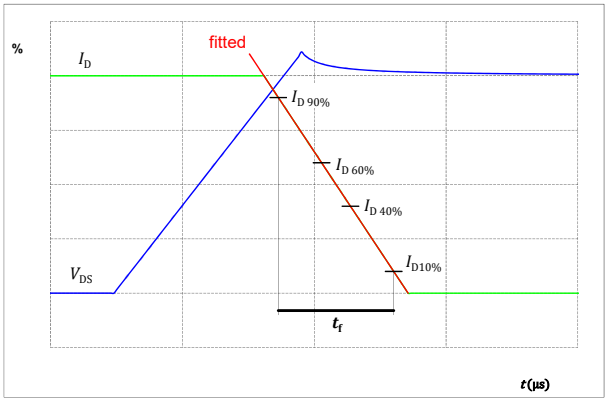
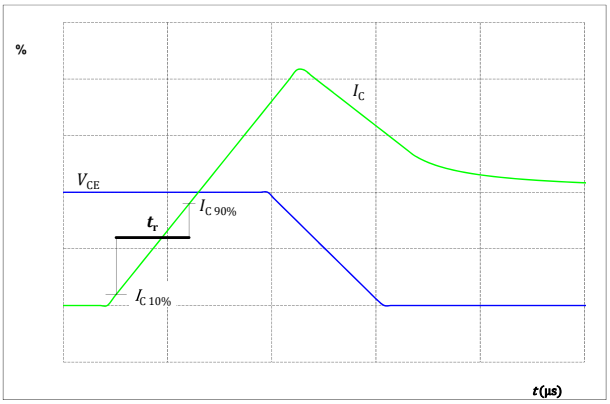


figure 26. MOSFET

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 27. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

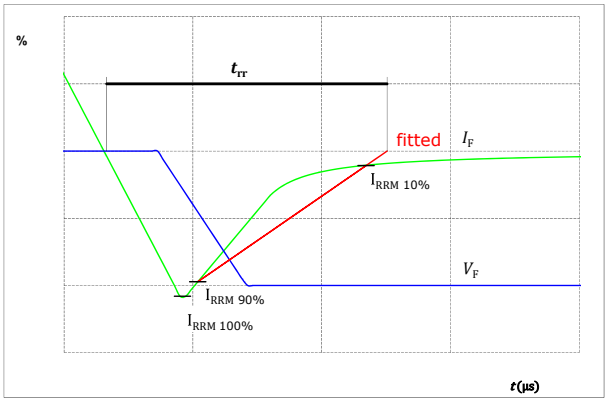


figure 28. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

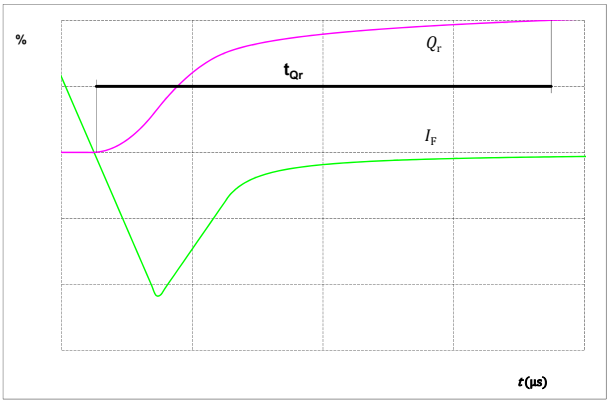
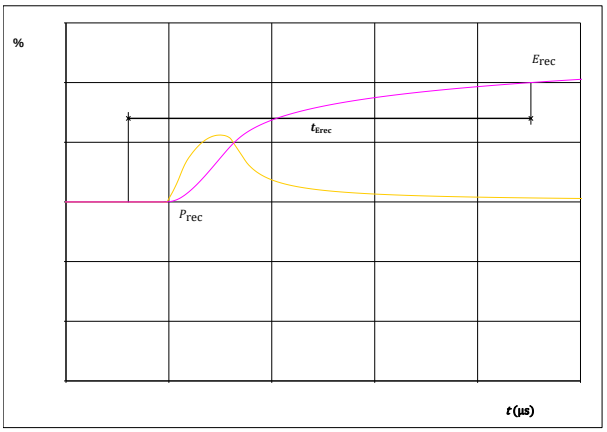


figure 29. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Ordering Code

Version	Ordering Code
Without thermal paste	10-PC124PA030MS-L629F76Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PC124PA030MS-L629F76Y-/7/

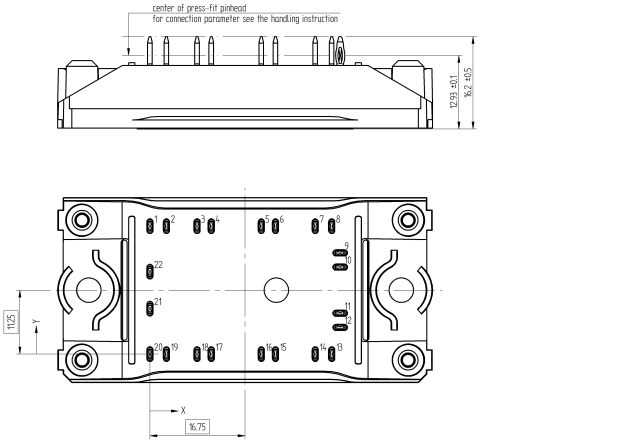
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTVV	LLLLL	SSSS	WWYY		

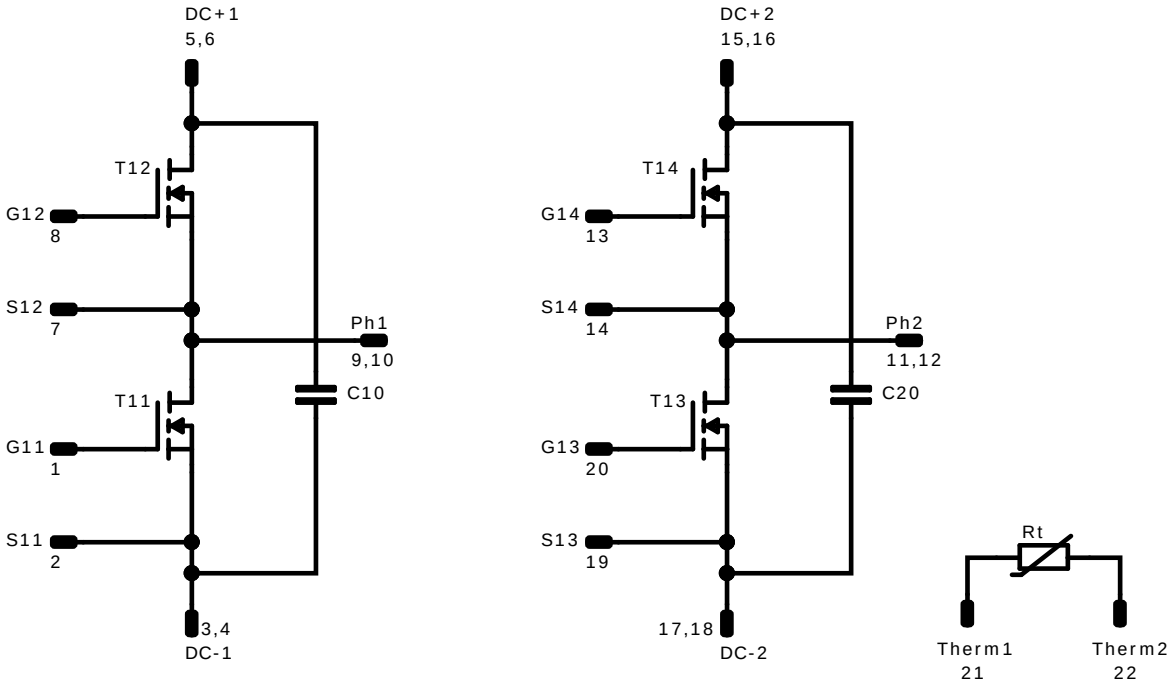
Outline

Pin table [mm]

Pin	X	Y	Function
1	0	22,5	G11
2	2,9	22,5	S11
3	8,3	22,5	DC-1
4	10,8	22,5	DC-1
5	19,6	22,5	DC+1
6	22,1	22,5	DC+1
7	29,1	22,5	S12
8	32	22,5	G12
9	33,5	17,8	Ph1
10	33,5	15,3	Ph1
11	33,5	7,2	Ph2
12	33,5	4,7	Ph2
13	32	0	G14
14	29,1	0	S14
15	22,1	0	DC+2
16	19,6	0	DC+2
17	10,8	0	DC-2
18	8,3	0	DC-2
19	2,9	0	S13
20	0	0	G13
21	0	8	Therm1
22	0	14,5	Therm2



Pinout



Identification					
ID	**Component**	**Voltage**	**Current**	**Function**	**Comment**
T11, T12, T13, T14	MOSFET	1200 V	30 mΩ	Inverter Switch	
C10, C20	Capacitor	1000 V		Capacitor (DC)	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PC124PA030MS-L629F76Y-D1-14	27 Aug. 2025	Initial Release	